Åakir AydoÄan

List of Publications by Year
in descending order

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131 papers	2,996 citations	172457 29 h-index	214800 47 g-index
132 all docs	132 docs citations	132 times ranked	1604 citing authors

#	Article	IF	Citations
1	Electrical characterization of Au/n-ZnO Schottky contacts on n-Si. Journal of Alloys and Compounds, 2009, 476, 913-918.	5.5	168
2	Fabrication and electrical characteristics of Schottky diode based on organic material. Microelectronic Engineering, 2008, 85, 1647-1651.	2.4	144
3	On the barrier inhomogeneities of polyaniline/p-Si/Al structure at low temperature. Applied Surface Science, 2005, 250, 43-49.	6.1	98
4	Some electrical properties of polyaniline/p-Si/Al structure at 300K and 77K temperatures. Microelectronic Engineering, 2008, 85, 278-283.	2.4	97
5	A new route for the synthesis of graphene oxideâ€“Fe3O4 (GOâ€“Fe3O4) nanocomposites and their Schottky diode applications. Journal of Alloys and Compounds, 2014, 585, 681-688.	5.5	94
6	Currentâ€“voltage and capacitanceâ€“voltage characteristics of polypyrrole/p-InP structure. Vacuum, 2005, 77, 269-274.	3.5	90
7	The effects of the temperature on the some parameters obtained from currentâ€“voltage and capacitanceâ€“voltage characteristics of polypyrrole/n-Si structure. Polymer, 2005, 46, 563-568.	3.8	77
8	Temperature dependence of reverse bias capacitanceâ€“voltage characteristics of Sn/p-GaTe Schottky diodes. Semiconductor Science and Technology, 2004, 19, 242-246.	2.0	76
9	High barrier Schottky diode with organic interlayer. Solid State Communications, 2012, 152, 381-385.	1.9	64
10	The barrier height enhancement of the Au/n-Si/Al Schottky barrier diode by electrochemically formed an organic Anthracene layer on n-Si. Superlattices and Microstructures, 2013, 56, 45-54.	3.1	62
11	On the some electrical properties of the non-ideal PPy/p-Si/Al structure. Polymer, 2005, 46, 10982-10988.	3.8	60
12	Series resistance determination of Au/Polypyrrole/p-Si/Al structure by currentâ€“voltage measurements at low temperatures. Materials Science and Engineering C, 2009, 29, 1486-1490.	7.3	57
13	Effect of 6MeV electron irradiation on electrical characteristics of the Au/n-Si/Al Schottky diode. Microelectronic Engineering, 2008, 85, 2299-2303.	2.4	55
14	Space charge limited current mechanism (SCLC) in the graphene oxideâ€“Fe3O4 nanocomposites/n-Si heterojunctions. Journal of Alloys and Compounds, 2015, 631, 261-265.	5.5	55
15	Room temperature deposition of XRD-amorphous TiO2 thin films: Investigation of device performance as a function of temperature. Ceramics International, 2018, 44, 11582-11590.	4.8	55
16	Electrical characterization of the Al/new fuchsin/n-Si organic-modified device. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 1411-1416.	2.7	49
17	The temperature dependence of currentâ€“voltage characteristics of the Au/Polypyrrole/p-Si/Al heterojunctions. Journal of Physics Condensed Matter, 2006, 18, 2665-2676.	1.8	44
18	Extraction of electronic parameters of Schottky diode based on an organic Orcein. Microelectronic Engineering, 2010, 87, 2525-2530.	2.4	44

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19	A facile growth of spray based ZnO films and device performance investigation for Schottky diodes: Determination of interface state density distribution. Journal of Alloys and Compounds, 2017, 708, 55-66.	5.5	43
20	Electronic parameters of high barrier Au/Rhodamine-101/n-Inp Schottky diode with organic Ä±nterlayer. Thin Solid Films, 2012, 520, 1944-1948.	1.8	38
21	Fabrication and electrical properties of Al/Safranin T/n-Si/AuSb structure. Semiconductor Science and Technology, 2008, 23, 075005.	2.0	37
22	Fabrication of spray derived nanostructured n-ZnO/p-Si heterojunction diode and investigation of its response to dark and light. Ceramics International, 2019, 45, 14794-14805.	4.8	36
23	Characterization of capacitanceâ€“frequency features of Sn/polypyrrole/n-Si structure as a function of temperature. Polymer, 2005, 46, 6148-6153.	3.8	35
24	Determination of contact parameters of Au/Carmine/n-Si Schottky device. Thin Solid Films, 2010, 518, 7156-7160.	1.8	35
25	Preparation and characterization of solâ€“gel-derived n-ZnO thin film for Schottky diode application. Applied Physics A: Materials Science and Processing, 2015, 119, 547-552.	2.3	34
26	Iâ€“Vâ€“T (currentâ€“voltageâ€“temperature) characteristics of the Au/Anthraquinone/p-Si/Al junction device. Journal of Alloys and Compounds, 2014, 584, 652-657.	5.5	33
27	The Effect of Mn Incorporation on the Structural, Morphological, Optical, and Electrical Features of Nanocrystalline ZnO Thin Films Prepared by Chemical Spray Pyrolysis Technique. Metallurgical and Materials Transactions A: Physical Metallurgy and Materials Science, 2015, 46, 2726-2735.	2.2	33
28	Optoelectronic properties of Co/pentacene/Si MIS heterojunction photodiode. Physica B: Condensed Matter, 2020, 597, 412408.	2.7	33
29	A study on non-stoichiometric p-NiOx/n-Si heterojunction diode fabricated by RF sputtering: Determination of diode parameters. Superlattices and Microstructures, 2016, 100, 924-933.	3.1	31
30	The effect of measurements and layer coating homogeneity of AB on the Al/AB/p-Si devices. Journal of Alloys and Compounds, 2019, 790, 388-396.	5.5	31
31	The electrical characteristics of the Fe3O4/Si junctions. Journal of Alloys and Compounds, 2013, 552, 437-442.	5.5	30
32	The effect of the electron irradiation on the series resistance of Au/Ni/6H-SiC and Au/Ni/4H-SiC Schottky contacts. Nuclear Instruments & Methods in Physics Research B, 2010, 268, 616-621.	1.4	29
33	Effect of temperature on the capacitanceâ€“frequency and conductanceâ€“voltage characteristics of polyaniline/p-Si/Al MIS device at high frequencies. Microelectronics Reliability, 2012, 52, 1362-1366.	1.7	29
34	The effects of the temperature on currentâ€“voltage characteristics of Sn/polypyrrole/n-Si structures. Synthetic Metals, 2005, 150, 15-20.	3.9	28
35	The comparison of Co/hematoxylin/n-Si and Co/hematoxylin/p-Si devices as rectifier for a wide range temperature. Materials Science in Semiconductor Processing, 2020, 113, 105039.	4.0	28
36	The barrier height inhomogeneity in identically prepared Pb/p-type Si Schottky barrier diodes. Semiconductor Science and Technology, 2003, 18, 642-646.	2.0	27

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37	The effect of Pb doping on the characteristic properties of spin coated ZnO thin films: Wrinkle structures. Materials Science in Semiconductor Processing, 2015, 40, 162-170.	4.0	26
38	The investigation of the electrical properties of Fe3O4/n-Si heterojunctions in a wide temperature range. Journal of Colloid and Interface Science, 2016, 473, 172-181.	9.4	26
39	Extraction of electronic parameters of Schottky diode based on an organic Indigotindisulfonate Sodium (IS). Solid State Communications, 2010, 150, 1592-1596.	1.9	25
40	Investigation of Structural, Morphological, Optical, and Electrical Properties of Al Doped ZnO Thin Films Via Spin Coating Technique. Synthesis and Reactivity in Inorganic, Metal Organic, and Nano Metal Chemistry, 2016, 46, 489-494.	0.6	25
41	Highly sensitive, self-powered photodetector based on reduced graphene oxide- polyvinyl pyrrolidone fibers (Fs)/p-Si heterojunction. Journal of Alloys and Compounds, 2021, 889, 161647.	5.5	23
42	Temperature-dependent C-V characteristics of Au/ZnO/n-Si device obtained by atomic layer deposition technique. Journal of Materials Science: Materials in Electronics, 2017, 28, 5880-5886.	2.2	22
43	Fabrication and electrical characterization of a silicon Schottky device based on organic material. Physica Scripta, 2009, 79, 035802.	2.5	21
44	Light-sensing behaviors of organic/n-Si bio-hybrid photodiodes based on malachite green (MG) organic dye. Journal of Materials Science: Materials in Electronics, 2020, 31, 21548-21556.	2.2	21
45	Synthesis and Characterization of Reduced Graphene Oxide/Rhodamine 101 (rGO-Rh101) Nanocomposites and Their Heterojunction Performance in rGO-Rh101/p-Si Device Configuration. Journal of Electronic Materials, 2018, 47, 329-336.	2.2	20
46	Influence of illumination intensity on electrical characteristics of Eosin y dye-based hybrid photodiode: comparative study. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	2.3	20
47	Fabrication and electrical properties of Al/aniline green/n-Si/AuSb structure. Materials Science in Semiconductor Processing, 2008, 11, 53-58.	4.0	19
48	Improving the performance of the organic solar cell and the inorganic heterojunction devices using monodisperse Fe3O4 nanoparticles. Optik, 2017, 142, 134-143.	2.9	19
49	Facile electrochemical-assisted synthesis of TiO2 nanotubes and their role in Schottky barrier diode applications. Superlattices and Microstructures, 2018, 113, 310-318.	3.1	19
50	The power conversion efficiency optimization of the solar cells by doping of (Au:Ag) nanoparticles into P3HT:PCBM active layer prepared with chlorobenzene and chloroform solvents. Materials Research Express, 2019, 6, 095104.	1.6	19
51	Reverse bias capacitanceâ€“voltage characteristics of Al/polyaniline/p-Si/Al structure as a function of temperature. Journal of Non-Crystalline Solids, 2008, 354, 4991-4995.	3.1	18
52	Performance improvement of n-TiO2/p-Si heterojunction by forming of n-TiO2/polyphenylene/p-Si anisotype sandwich heterojunction. Materials Science in Semiconductor Processing, 2021, 121, 105436.	4.0	18
53	Self-powered ZrO₂ nanofibers/n-Si photodetector with high on/off ratio for detecting very low optical signal. Journal Physics D: Applied Physics, 2021, 54, 475101.	2.8	18
54	Discrepancies in barrier heights obtained from currentâ€“voltage (IV) and capacitanceâ€“voltage (CV) of Au/PNoMPhPPy/n-GaAs structures in wide range of temperature. Journal of Materials Science: Materials in Electronics, 2022, 33, 12210-12223.	2.2	17

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55	Electron irradiation effects on the organic-on-inorganic silicon Schottky structure. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2008, 593, 544-549.	1.6	16
56	Electrochemical growth of GaTe onto the p-type Si substrate and the characterization of the Sn/GaTe Schottky diode as a function of temperature. Thin Solid Films, 2014, 550, 40-45.	1.8	16
57	The performance of chitosan layer in Au/n-Si sandwich structures as a barrier modifier. Polymer Testing, 2020, 89, 106546.	4.8	16
58	An examination of correlation between characteristic and device performance of ZnO films as a function of La content. Vacuum, 2018, 157, 497-507.	3.5	15
59	Effect of illumination intensity on the characteristics of Co/Congo Red/p-Si/Al hybrid photodiode. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	2.3	15
60	Modification of barrier diode with cationic dye for high power applications. Optik, 2021, 232, 166598.	2.9	15
61	Self-powered photosensor based on curcumin:reduced graphene oxide (CU:rGO)/n-Si heterojunction in visible and UV regions. Journal of Alloys and Compounds, 2022, 915, 165428.	5.5	15
62	A comparative study of the ZnO Fibers-based photodetectors on n-Si and p-Si. Journal Physics D: Applied Physics, 2022, 55, 395102.	2.8	15
63	The effect of electron irradiation on the electrical characteristics of the Aniline Blue/n-Si/Al device. Solid State Sciences, 2011, 13, 1369-1374.	3.2	14
64	The synthesis of SrTiO₃nanocubes and the analysis of nearly ideal diode application of Ni/SrTiO₃nanocubes/n-Si heterojunctions. Materials Research Express, 2018, 5, 015060.	1.6	14
65	Comparison of n and p type Si-based Schottky photodiode with interlayered Congo red dye. Materials Science in Semiconductor Processing, 2021, 135, 106045.	4.0	14
66	The Synthesis of the Fe3O4 Nanoparticles and the Analysis of the Currentâ€“Voltage Measurements on Au/Fe3O4/p-Si Schottky Contacts in a Wide Temperature Range. Metallurgical and Materials Transactions A: Physical Metallurgy and Materials Science, 2013, 44, 3809-3814.	2.2	13
67	The analysis of the currentâ€“voltage characteristics of the high barrier Au/Anthracene/n-Si MIS devices at low temperatures. Materials Chemistry and Physics, 2014, 143, 545-551.	4.0	13
68	Phenol red based hybrid photodiode for optical detector applications. Solid-State Electronics, 2020, 171, 107864.	1.4	13
69	Co/aniline blue/silicon sandwich hybrid heterojunction for photodiode and low-temperature applications. Journal of Sandwich Structures and Materials, 2021, 23, 2547-2565.	3.5	13
70	Investigation of electrical properties of Ni/Crystal Violet (C25H30ClN3)/n-Si/Al diode as a function of temperature. Journal of Alloys and Compounds, 2018, 763, 622-628.	5.5	12
71	Effect of NiO_xâ€™s film thickness on the electrical properties of Ni/pâ€“NiOx/n-Si structures. Journal of Sandwich Structures and Materials, 2021, 23, 1383-1402.	3.5	12
72	Thermal sensing capability of metal/composite-semiconductor framework device with the low barrier double Gaussian over wide temperature range. Sensors and Actuators A: Physical, 2021, 332, 113117.	4.1	12

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73	Long-Term Stable, Selfâ€Powered and Highly Sensitive Photodetectors Based on the ZnO:ZrO2 Composite Fibers (Fs)/N-Si Heterojunction. Jom, 2022, 74, 3091-3102.	1.9	12
74	Investigation of the switching phenomena in Ga2Te3 single crystals. Journal of Crystal Growth, 2005, 279, 110-113.	1.5	11
75	Fabrication and electrical properties of Al/phenolsulfonphthalein/n-Si/AuSb structure. Vacuum, 2008, 82, 1264-1268.	3.5	11
76	The effects of 12MeV electron irradiation on the electrical characteristics of the Au/Aniline blue/p-Si/Al device. Microelectronics Reliability, 2011, 51, 2216-2222.	1.7	11
77	Influence of 12MeV electron irradiation on the electrical and photovoltaic properties of Schottky type solar cell based on Carmine. Radiation Physics and Chemistry, 2011, 80, 869-875.	2.8	11
78	Temperature-dependent currentâ€“voltage measurements of Au/C9H7N/p-Si: Characterization of a metalâ€“organic-semiconductor device. Materials Science in Semiconductor Processing, 2015, 34, 58-64.	4.0	11
79	Analysis on the temperature dependent electrical properties of Cr/Graphene oxide-Fe3O4 nanocomposites/n-Si heterojunction device. Diamond and Related Materials, 2020, 108, 107933.	3.9	11
80	Investigation the Performance of Cr-Doped ZnO Nanocrystalline Thin Film in Photodiode Applications. Jom, 2022, 74, 777-786.	1.9	11
81	Analysis of temperature dependent electrical characteristics of Au/GaSe Schottky barrier diode improved by Ce-doping. Sensors and Actuators A: Physical, 2020, 315, 112264.	4.1	10
82	A comparative study on the effect of monodisperse Au and Ag nanoparticles on the performance of organic photovoltaic devices. Optical Materials, 2021, 116, 111082.	3.6	10
83	Dependence of electrical parameters of co/gold-chloride/p-Si diode on frequency and illumination. Optical Materials, 2021, 121, 111613.	3.6	10
84	Synthesis characterization of SnO2 nanofibers (NFs) and application of high-performing photodetectors based on SnO2 NFs/n-Si heterostructure. Sensors and Actuators A: Physical, 2022, 342, 113631.	4.1	10
85	A study of the rectifying behaviour of aniline green-based Schottky diode. Microelectronic Engineering, 2010, 87, 187-191.	2.4	9
86	Schottky diode performance of an Au/Pd/GaAs device fabricated by deposition of monodisperse palladium nanoparticles over a p-type GaAs substrate. Materials Science in Semiconductor Processing, 2014, 27, 163-169.	4.0	9
87	Development of a hybrid photodetector device between pyruvic acid (CH₃COCOOH) and silicon. Semiconductor Science and Technology, 2021, 36, 105004.	2.0	9
88	Improving light-sensing behavior of Cu/n-Si photodiode with Human Serum Albumin: Microelectronic and dielectric characterization. Optik, 2021, 241, 167069.	2.9	9
89	The photosensitive activity of organic/inorganic hybrid devices based on Aniline Blue dye: Au nanoparticles (AB@Au NPs). Sensors and Actuators A: Physical, 2021, 330, 112856.	4.1	9
90	Density Functional Theory Calculations of Pinus brutia Derivatives and Its Response to Light in a Au/n-Si Device. Energies, 2021, 14, 7983.	3.1	9

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91	The light detection performance of the congo red dye in a Schottky type photodiode. Chemical Physics Letters, 2022, 800, 139673.	2.6	9
92	Electrical properties of polypyrrole/p-InP structure. Journal of Polymer Science, Part B: Polymer Physics, 2006, 44, 1572-1579.	2.1	8
93	A novel polyphenol-based ferromagnetic polymer: synthesis, characterization and Schottky diode applications. Applied Physics A: Materials Science and Processing, 2015, 119, 1301-1309.	2.3	8
94	Role of the Au and Ag nanoparticles on organic solar cells based on P3HT:PCBM active layer. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	2.3	8
95	On the studies of capacitanceâ€“voltage and impedance spectroscopy of an Ni/(GO-Fe₃O₄)/n-Si heterojunction device over a wide temperature range. Semiconductor Science and Technology, 2020, 35, 105012.	2.0	8
96	A comparative study on electrical characteristics of Ni/n-Si and Ni/p-Si Schottky diodes with Pinus Sylvestris Resin interfacial layer in dark and under illumination at room temperature. Optical Materials, 2021, 119, 111380.	3.6	8
97	An Investigation of Spray Deposited CdO Films and CdO/p-Si Heterojunction at Different Substrate Temperatures. Jom, 2021, 73, 566-573.	1.9	8
98	Synthesis of nickel nanoparticles-deposited strontium titanate nanocubes (Ni-STO) and heterojunction electrical applications over a wide temperature range. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2021, 274, 115479.	3.5	8
99	Optical absorption of the anthracene and temperature-dependent capacitanceâ€“voltage characteristics of the Au/anthracene/ n -Si heterojunction in metalâ€“organic-semiconductor configuration. Physica E: Low-Dimensional Systems and Nanostructures, 2015, 74, 505-509.	2.7	7
100	Improving the rectifying properties of metal/semiconductor junction using novel material: Zam-zam. Sensors and Actuators A: Physical, 2016, 248, 22-28.	4.1	7
101	Hydrothermal growth of ZnO nanoparticles under different conditions. Philosophical Magazine Letters, 2016, 96, 45-51.	1.2	7
102	The electrical and dielectric properties of the magnetite nanoparticles supported graphene-oxide/n-Si MOS type device that operates across a wide temperature range. Sensors and Actuators A: Physical, 2021, 331, 112989.	4.1	7
103	The electrical and dielectric characterization of the Co/ZnO-Rods/p-Si heterostructure depending on the frequency. Journal of Materials Science: Materials in Electronics, 2022, 33, 6059-6069.	2.2	7
104	Effects of PEDOT:PSS andÂcrystalÂvioletÂinterfaceÂlayers onÂcurrent-voltageÂperformance of SchottkyÂbarrierÂdiodes as aÂfunction ofÂtemperature andÂvariation ofÂdiodeÂcapacitance withÂfrequency. Current Applied Physics, 2022, 39, 173-182.	2.4	7
105	Photo-sensor characteristics of tannic acid (C76H52O46)/n-Si hybrid bio-photodiode for visible and UV lights detection. Optics and Laser Technology, 2022, 153, 108194.	4.6	7
106	Enhanced Electrical and Optical Characteristics of Co/Phenol Red (PR)/Silicon Hybrid Heterojunction for Photodiode and Thermal Applications. Journal of Electronic Materials, 2020, 49, 4952-4961.	2.2	6
107	On thermal and optical sensor applications of chitosan molecule in the Co/Chitosan/p-Si hybrid heterojunction design. Journal of Materials Science: Materials in Electronics, 2021, 32, 6586-6597.	2.2	6
108	The performance of the anthraquinone/p-Si and the pyridine/p-Si rectifying device under X-ray irradiation. Materials Chemistry and Physics, 2016, 183, 516-523.	4.0	5

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109	Synthesis and characterization of p-GaSe thin films and the analyses of Iâ€“V and Câ€“V measurements of p-GaSe/p-Si heterojunction under electron irradiation. Radiation Effects and Defects in Solids, 2017, 172, 650-663.	1.2	5
110	Investigation of neodymium rare earth element doping in spray-coated zinc oxide thin films. Journal of Materials Science: Materials in Electronics, 2021, 32, 1379-1391.	2.2	5
111	The heterojunction diode application of mesoporous graphitic carbon nitride (mpg-C3N4). Superlattices and Microstructures, 2021, 157, 106991.	3.1	5
112	Analysis of the temperature dependent electrical parameters of the heterojunction obtained with Au nanoparticles decorated perovskite strontium titanate nanocubes. Journal of Alloys and Compounds, 2022, 914, 165140.	5.5	5
113	Conductance and series resistance measurements of polyaniline/p-Si and polypyrrole/InP junction devices. Physica E: Low-Dimensional Systems and Nanostructures, 2012, 46, 38-42.	2.7	4
114	Synthesis, characterization and diode application of poly(4-(1-(2-phenylhydrazono)ethyl)phenol). Journal of Materials Chemistry C, 2015, 3, 5803-5810.	5.5	4
115	Schottky Diode Applications of the Fast Green FCF Organic Material and the Analyze of Solar Cell Characteristics. Journal of Physics: Conference Series, 2016, 707, 012052.	0.4	4
116	Synthesis and characterization of ZnO micro-rods and temperature-dependent characterizations of heterojunction of ZnO microrods/CdTe and ZnO microrods/ZnTe structures. Sensors and Actuators A: Physical, 2017, 261, 56-65.	4.1	4
117	Temperature dependent electronic transport properties of heterojunctions formed between perovskite SrTiO3 nanocubes and silicon. Journal of Materials Science: Materials in Electronics, 2020, 31, 20833-20846.	2.2	4
118	Light Sensitive Properties and Temperature-Dependent Electrical Performance of n-TiO2/p-Si Anisotype Heterojunction Electrochemically Formed TiO2 on p-Si. Journal of Electronic Materials, 2021, 50, 5184.	2.2	4
119	On the investigation of the electro-optical sensor potential of Boswellia serrata resin. Optical Materials, 2021, 117, 111154.	3.6	4
120	Fabrication and electrical characterisation of the Ti/GaTe/p-Si device under 18ÂMeV electron irradiation. Journal of Radioanalytical and Nuclear Chemistry, 2014, 300, 1113-1120.	1.5	3
121	Electrochemical impedance spectroscopy analysis of ZnO films: the effect of Mg doping. Philosophical Magazine Letters, 2019, 99, 243-252.	1.2	3
122	Current-transport mechanisms in the Au/GaSe:Nd Schottky contact. Journal of Materials Science: Materials in Electronics, 2020, 31, 5198-5204.	2.2	3
123	Pomegranate derivative dye/silicon hybrid photodiode for sensor applications. Sensors and Actuators A: Physical, 2022, 345, 113669.	4.1	3
124	The effect of temperature on the electrical characterization of a poly(phenoxy-imine)/p-silicon heterojunction. E-Polymers, 2016, 16, 75-82.	3.0	2
125	THE INFLUENCE OF HIGH-ENERGY ELECTRONS IRRADIATION ON SURFACE OF n-GaP AND ON Au/n-GaP/Al SCHOTTKY BARRIER DIODE. Surface Review and Letters, 2018, 25, 1850064.	1.1	2
126	Optical and electrical characterization of organic solar cells obtained using gold and silver metal nanoparticles. Materials Today: Proceedings, 2021, 46, 6986-6990.	1.8	2

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127	Fabrication and characterization of Al/n-Si/Al schottky diode with rGO interfacial layer obtained by using spin coating method. Materials Today: Proceedings, 2021, 46, 6899-6903.	1.8	2
128	Schottky barrier engineering in metal/semiconductor structures for high thermal stability. Semiconductor Science and Technology, 2021, 36, 075020.	2.0	2
129	Influence of thickness of the sputtered diamond-like carbon (DLC) on electronic and dielectric parameters of the Au/DLC/n-Si heterojunction. Journal of Materials Science: Materials in Electronics, 0, , 1.	2.2	2
130	Effects of the photoactive layer properties and current transmission mechanism on optical and electrical characteristics of organic photovoltaic. Optik, 2021, 241, 166937.	2.9	2
131	Growth of InSe:Mn semiconductor crystals by Bridgmanâ€“Stockbarger technique and analysis of electron irradiation effects on Sn/InSe:Mn Schottky diodes. Radiation Effects and Defects in Solids, 2016, 171, 528-543.	1.2	0